

2SJ244

Silicon P Channel MOS FET

REJ03G0853-0200
(Previous: ADE-208-1187)
Rev.2.00
Sep 07, 2005

Description

High speed power switching

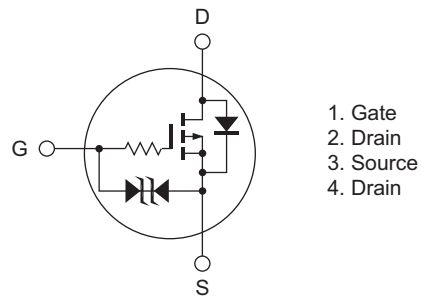
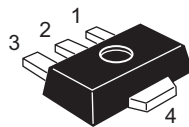
Low voltage operation

Features

- Very Low on-resistance
- High speed switching
- Suitable for camera or VTR motor drive circuit, power switch, solenoid drive and etc.

Outline

RENESAS Package code: PLZZ0004CA-A
(Package name: UPAK®)



1. Gate
2. Drain
3. Source
4. Drain

Note: Marking is "JY".

*UPAK is a trademark of Renesas Technology Corp.

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V_{DSS}	-12	V
Gate to source voltage	V_{GSS}	± 7	V
Drain current	I_D	± 2	A
Drain peak current	$I_{D(pulse)}$ ^{Note 1}	± 4	A
Channel dissipation	P_{ch} ^{Note 2}	1	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Notes: 1. $PW \leq 100 \mu s$, duty cycle $\leq 10\%$ 2. Value on the alumina ceramic board ($12.5 \times 20 \times 0.7 \text{ mm}$)

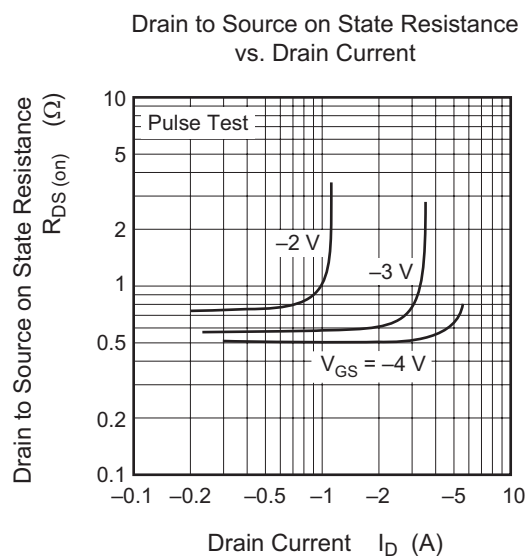
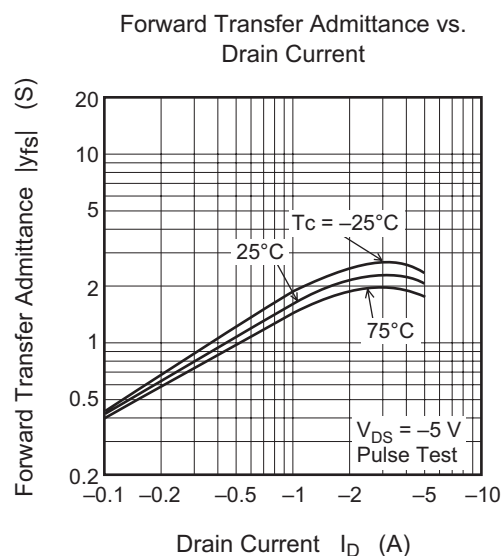
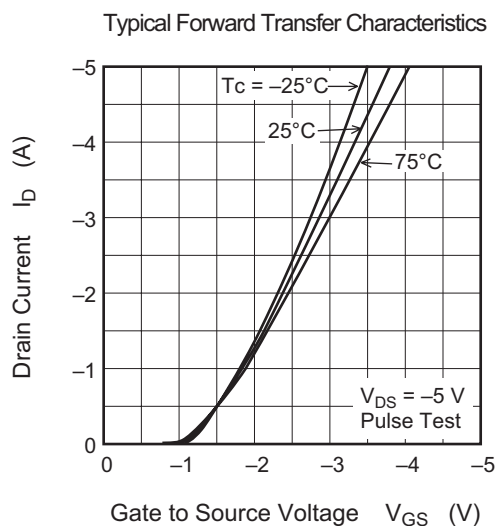
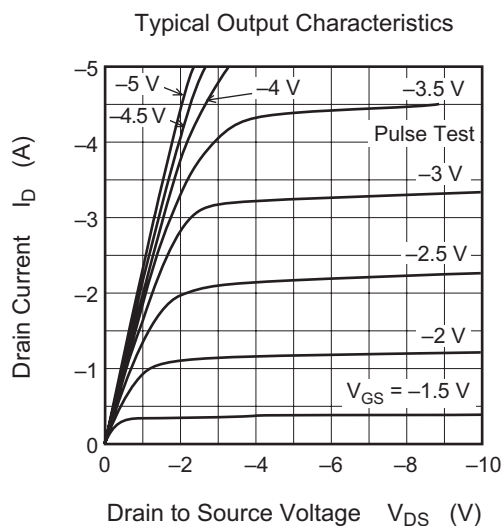
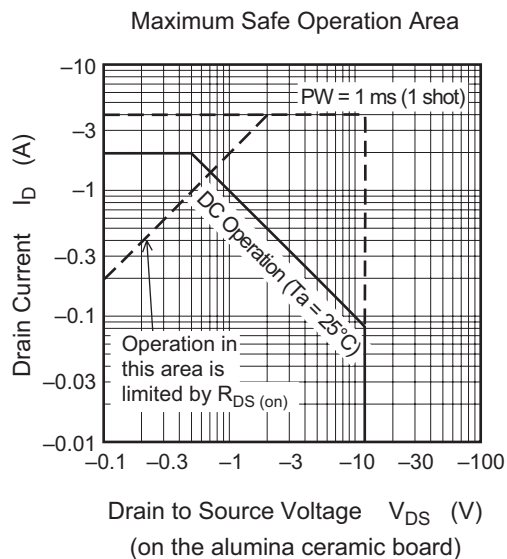
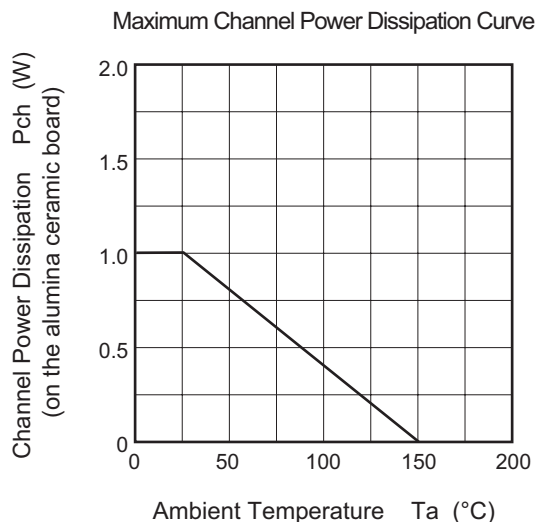
Electrical Characteristics

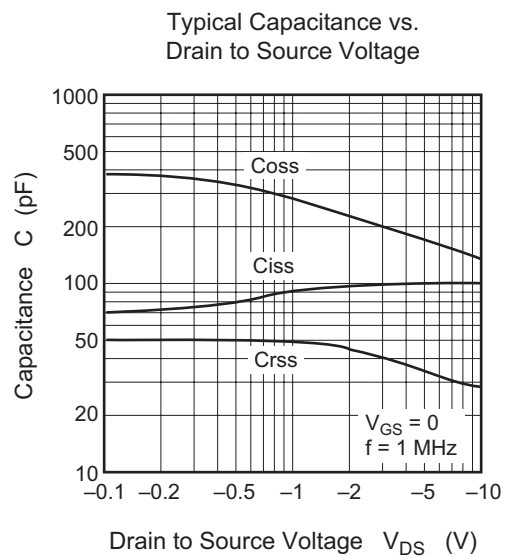
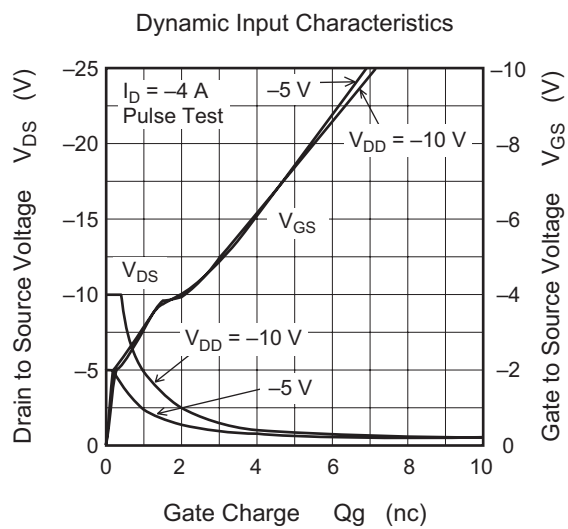
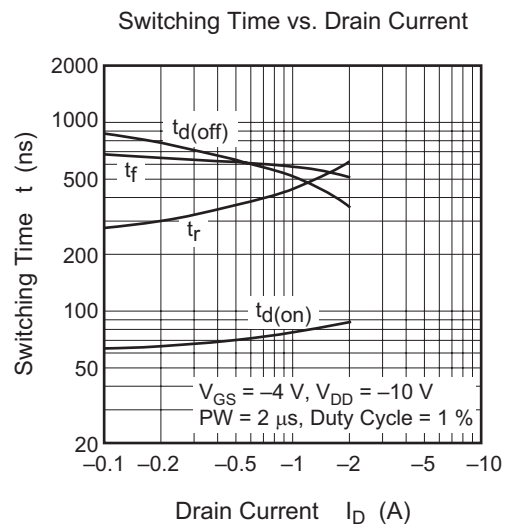
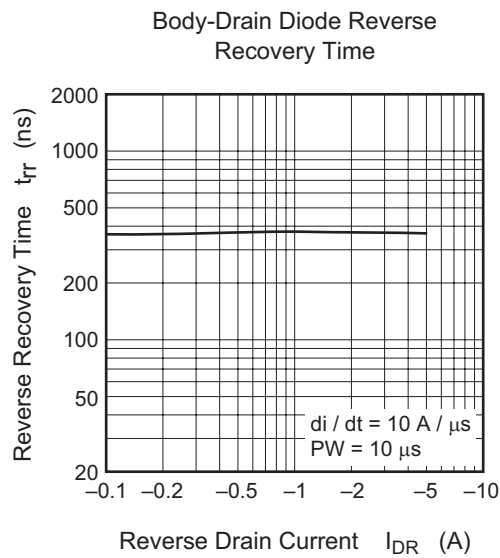
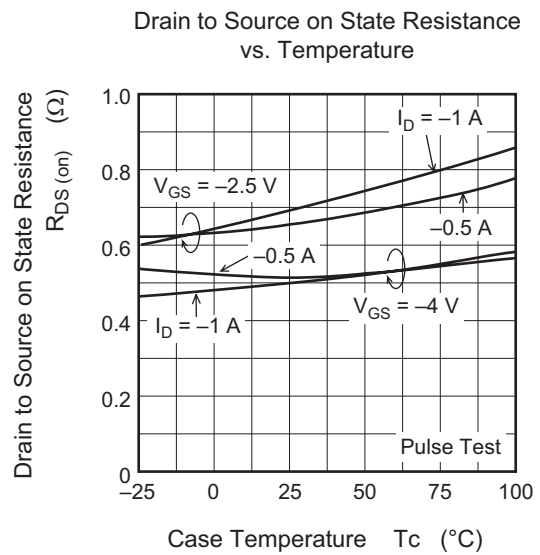
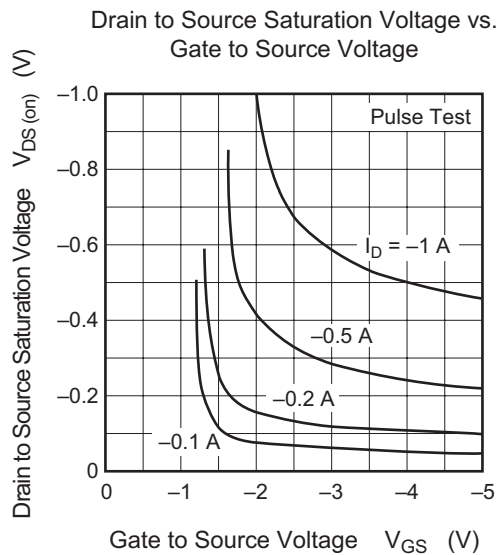
(Ta = 25°C)

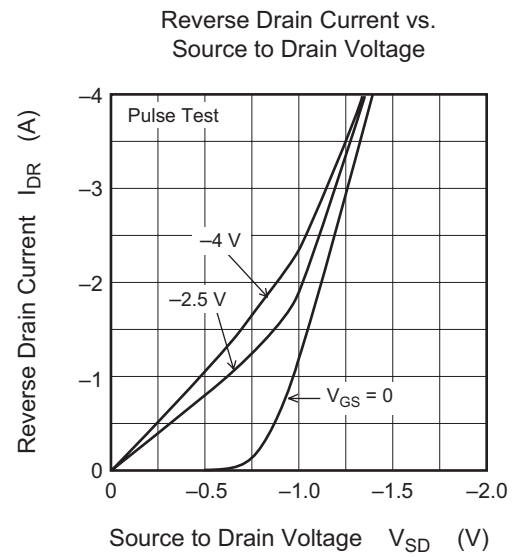
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-12	—	—	V	$I_D = -1 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 7	—	—	V	$I_G = \pm 10 \mu A$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 5	μA	$V_{GS} = \pm 6 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	-1	μA	$V_{DS} = -8 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-0.4	—	-1.4	V	$I_D = -100 \mu A$, $V_{DS} = -5 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)1}$	—	0.65	0.9	Ω	$I_D = -0.5 \text{ A}$, $V_{GS} = -2.5 \text{ V}$ ^{Note 3}
	$R_{DS(on)2}$	—	0.5	—	Ω	$I_D = -1 \text{ A}$, $V_{GS} = -4 \text{ V}$ ^{Note 3}
Forward transfer admittance	$ y_{fs} $	—	1.8	—	S	$I_D = -1 \text{ A}$, $V_{DS} = -5 \text{ V}$ ^{Note 3}
Input capacitance	C_{iss}	—	100	—	pF	$V_{DS} = -5 \text{ V}$
Output capacitance	C_{oss}	—	168	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	35	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	365	—	ns	$I_D = -0.2 \text{ A}$ ^{Note 3}
Turn-off delay time	$t_{d(off)}$	—	1450	—	ns	$V_{in} = -4 \text{ V}$, $R_L = 51 \Omega$
Body to drain diode forward voltage	V_{DF}	—	—	7	V	$I_F = 4 \text{ A}$ ^{Note 3} , $V_{GS} = 0$

Note: 3. Pulse test

Main Characteristics







Unit: mm

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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